

**DMG8880LSS** 

Lead-free Green

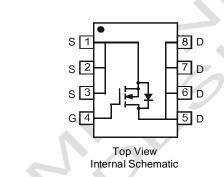
### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)



### Ordering Information (Note 4)

Part Number	Case	Packaging
DMG8880LSS-13	SO-8	2500 / Tape & Reel

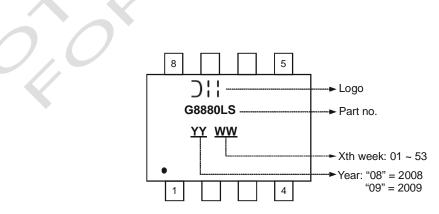
Notes:

Top View

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

<1000ppm antimony compounds. 4. For packaging details, go to our website at http://www.diodes.com.

### **Marking Information**





# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	ID	11.6 8.5	А
Pulsed Drain Current (Note 6)			IDM	80	А

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.43	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 5)	R•JA	87	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

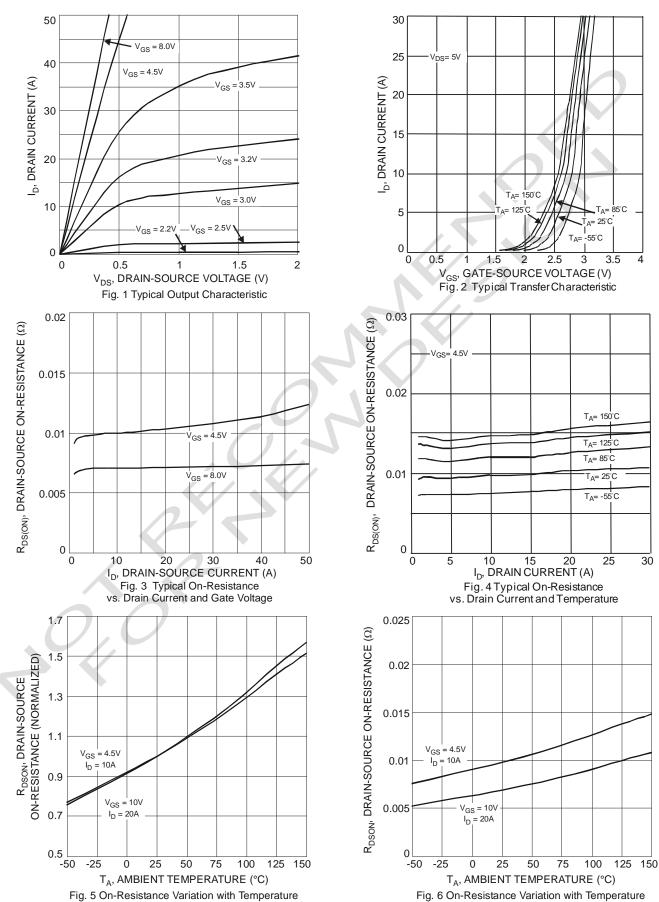
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			- 71-				
Drain-Source Breakdown Voltage	BVDSS	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current $T_J = 25^{\circ}C$	I <sub>DSS</sub>	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						-	
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	1.5	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	P		7.0	10 14	m∙	$V_{GS} = 10V, I_D = 11.6A$	
Static Drain-Source On-Nesistance	R <sub>DS (ON)</sub>	-	9.6			$V_{GS} = 4.5V, I_D = 10.7A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 2.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	1289	-	pF		
Output Capacitance	Coss	-	187	-	pF	─ V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, ─ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	162	-	pF	1 = 1.000112	
Gate Resistance	R <sub>g</sub>	-	0.97	-	•	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge at 10V	Qg	-	27.6	-	nC	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 11.6A, I_G = 1.0mA$	
Total Gate Charge at 5V	Qg	-	14.4	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	3.6	-	nC	$-V_{GS} = 5V, V_{DS} = 15V,$ $-I_{D} = 11.6A, I_{G} = 1.0mA$	
Gate-Drain Charge	Q <sub>gd</sub>	-	4.9	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	7.04	-	ns		
Turn-On Rise Time	tr	-	17.52	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	36.13	-	ns	$R_{GS} = 11^{\bullet}$ , $I_D = 11.6A$	
Turn-Off Fall Time	t <sub>f</sub>	-	19.67	-	ns		

Notes:

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

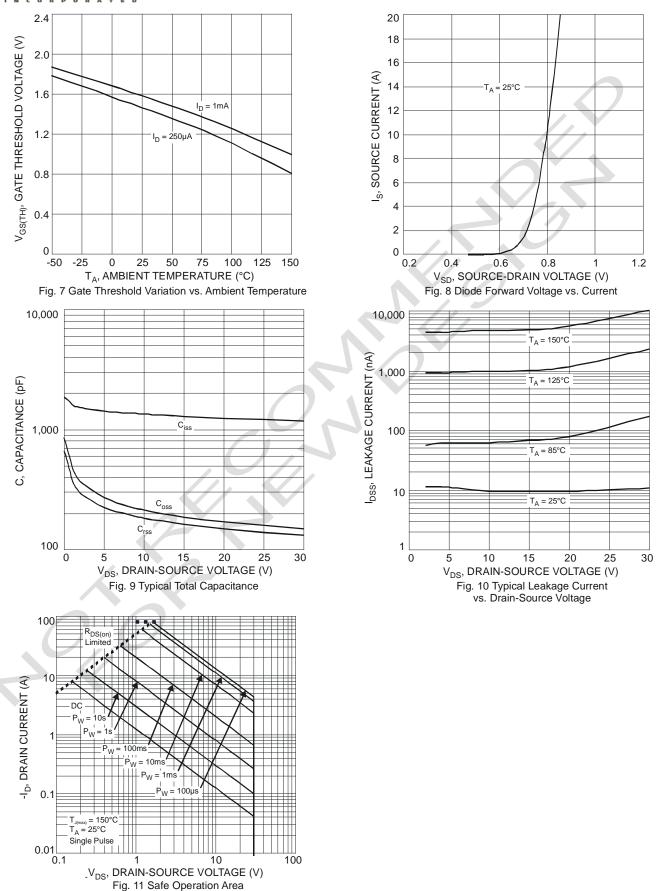
Repetitive rating, pulse width limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



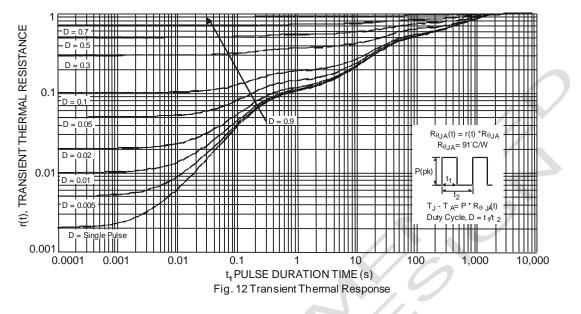




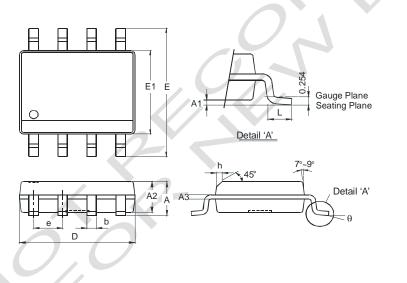
DMG8880LSS





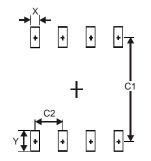


**Package Outline Dimensions** 



SO-8					
Dim	Min	Max			
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	-	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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